L Number	Hits	Search Text	DB	Time stamp
1	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	0	5233291.pn. and synthesis	USPAT;	2002/12/10 10:08
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
3	o	5233291.pn. and switch\$5	USPAT;	2002/12/10 10:11
1		See	US-PGPUB;	2002, 12, 10 10.11
			EPO; JPO;	
1	1		DERWENT;	
	•		IBM_TDB	
4	0	5233291.pn. and select\$5	USPAT;	2002/12/10 10:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
-	155	//!!	IBM_TDB	2002/12/10 10:13
5	155	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or	USPAT; US-PGPUB;	2002/12/10 10:13
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
ř.		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	1
	1	(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5		
6	107	((("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:15
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	į
		(capacit\$4/voltage)) and characteristic\$5		
7	54	<pre>and capacit\$5) and (switch\$5 or select\$5) ((("metal/insulator/semiconductor") or</pre>	USPAT;	2002/12/10 10:28
']	("metal-insulator-semiconductor")or	US-PGPUB;	2002/12/10 10.20
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	ł
1		(capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	_	
		and capacit\$5) and ((switch\$5 or		
		select\$5) same (capacit\$5))		
8	122	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2002/12/10 10:30
		("metal-insulator-semiconductor")or	US-PGPUB;	
(I)4		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO; DERWENT;	
		or (capacit\$4 adj voltage) or (capacit\$4-voltage) or	IBM TDB	
1		(capacit\$4/voltage)) and characteristic\$5	-2	
		and capacit\$5) and ((switch\$5 or select\$5		
		or elect\$5) same (capacit\$5))		
9	68	(((("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:30
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
	1	(capacit\$4/voltage)) and characteristic\$5		
		<pre>and capacit\$5) and ((switch\$5 or select\$5 or elect\$5) same (capacit\$5))) not</pre>		
	1	(((("metal/insulator/semiconductor") or		
		("metal-insulator-semiconductor") or		
		("MIS") or ("MAIS")) same (("C-V") or (CV)		
		or (capacit\$4 adj voltage) or		
		(capacit\$4-voltage) or		
-		(capacit\$4/voltage)) and characteristic\$5		, ,
		and capacit\$5) and ((switch\$5 or		
L		select\$5) same (capacit\$5)))	<u> </u>	L

-	46	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 12:03
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same ((("C-V") or (CV)) near3	EPO; JPO;	
		characteristic\$5) same capacit\$5	DERWENT;	i
		Characteristroyo, Same Sapasasy	IBM TDB	
	37	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 11:46
-	3'	("metal-insulator-semiconductor") or	US-PGPUB;	2002/12/03 11.40
		("MIS")) and ("LCR" adj meter)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1	"4083254".PN.	USPAT;	2002/12/09 11:50
			US-PGPUB	
-	1	"4322979".PN.	USPAT;	2002/12/09 11:50
			US-PGPUB	
_	1	"4681451".PN.	USPAT;	2002/12/09 11:50
	_	.002.02	US-PGPUB	
_	72	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:03
_	12		US-PGPUB;	2002/12/03 14.03
		("metal-insulator-semiconductor")or		1
	1	("MIS")) same ((("C-V") or (CV) or	EPO; JPO;	1
	1	(capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) near3		1
		characteristic\$5) same capacit\$5	}	1
l –	3	5701088.bi,uref.	USPAT;	2002/12/09 13:37
i			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
	4	"6177826"	USPAT;	2002/12/09 12:34
-	4	01//820	US-PGPUB;	2002/12/03 12.34
				j ·
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	į.
-	23	"5175445"	USPAT;	2002/12/09 12:35
			US-PGPUB;	
1			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
l _	3	(("6177826") or ("5175445") or	USPAT;	2002/12/09 12:35
i	3	("5107137")).PN.	US-PGPUB	
	14	5233291.bi,uref.	USPAT;	2002/12/09 14:00
-	14	5255291.D1, ulet.	US-PGPUB;	2002/12/03 14.00
			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	2	5233291.pn.	USPAT;	2002/12/10 10:03
			US-PGPUB;	
[}		EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	1	"5065103".PN.	USPĀT;	2002/12/09 14:00
[1	3003403 .14.	US-PGPUB	-30=, -=, 03 =00
			USPAT;	2002/12/09 14:01
-	1	"4992728".PN.	US-PGPUB	2002/12/09 14.01
	1		1	2002/12/00 14:01
j -	1	"4941753".PN.	USPAT;	2002/12/09 14:01
1		·	US-PGPUB	
i -	1	"4891584".PN.	USPAT;	2002/12/09 14:01
	1		US-PGPUB	
_	154	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:05
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same (("C-V") or (CV) or	EPO; JPO;	
		(capacit\$4 adj voltage) or	DERWENT;	
l		(capacit;4 adj voltage) or	IBM TDB	1
1		(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5	12100	
!				
	1	and capacit\$5	1	L

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				2002/12/10 10 12
-	155	(("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:12
		<pre>("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV)</pre>	US-PGPUB; EPO; JPO;	
			DERWENT;	
		or (capacit\$4 adj voltage) or (capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	1011_100	
		and capacit\$5		
1_	12	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:35
	12	("metal-insulator-semiconductor")or	US-PGPUB;	2002, 22, 11
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
1		(capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	_	
		and capacit\$5) and synthesis		
-	53	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:43
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and "nm"	IICDAM.	2002/12/09 15:29
-	1	5233291.pn. and "MIS"	USPAT; US-PGPUB;	2002/12/09 13:29
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	5233292.pn.	USPAT;	2002/12/09 15:30
	[323232.p	US-PGPUB:	
			EPO; JPO;	
			DERWENT;	!
	-		IBM TDB	
_	2	5233291.pn.	USPAT;	2002/12/09 15:43
			US-PGPUB;	
Ī			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 15:44
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO; DERWENT;	
		or (capacit\$4 adj voltage) or (capacit\$4-voltage) or	IBM TDB	
		(capacit \$4/voltage)) and characteristic \$5	150.	
		and capacit\$5) and (("4083254".PN. or		
		three) adj nm)		i
_	ا و	(("4083254".PN. or three) adj nm)	USPAT;	2002/12/10 07:14
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	0000/10/10 07 07
-	1	5233291.pn. and MIS	USPAT;	2002/12/10 07:27
			US-PGPUB;	
			EPO; JPO;	
	}		DERWENT;	
1_	6860	motohiro.in.	USPAT;	2002/12/10 07:27
-	0860	motomito.in.	US-PGPUB;	2002/12/10 0/.2/
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	6828	motohiro.inv.	USPAT;	2002/12/10 07:28
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	motohiro.inv. and ("MAIS")	USPĀT;	2002/12/10 07:50
			US-PGPUB;	
	1		EPO; JPO;	
1			DERWENT;	
	1		IBM TDB	<u> </u>